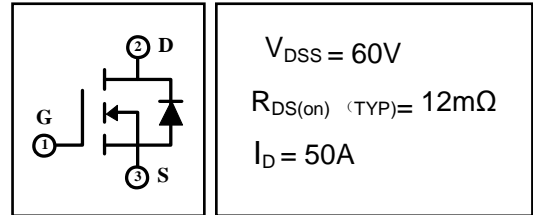


50A 60V N-channel Enhancement Mode Power MOSFET

1 Description

These N-channel Enhanced VDMOSFETs Used advanced trench technology design, provided excellent RDSON and low gate charge. Which accords with the RoHS standard.

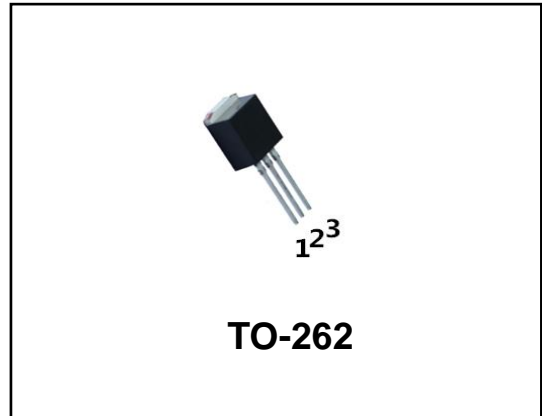


2 Features

- Fast Switching
- Low ON Resistance($R_{DS(on)} \leq 18m\Omega$)
- Low Gate Charge(Typical:17nC)
- Low Reverse Transfer Capacitances(Typical:150pF)
- 100% Single Pulse Avalanche Energy Test
- 100% ΔV_{DS} Test

3 Applications

- Power switching applications
- DC-DC Convertors
- UPS power supply
- Load switch



4 Electrical Characteristics

4.1 Absolute Maximum Rating ($T_c=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT	
Maximum Drain-Source DC Voltage	V_{DS}	60	V	
Maximum Gate-Drain Voltage	V_{GS}	± 20	V	
Drain Current(continuous)	I_D ($T=25^\circ\text{C}$) ($T=100^\circ\text{C}$)	66	A	
		50	A	
Drain Current(Pulsed) ^(Note 1)	I_{DM}	250	A	
Single Pulse Avalanche Energy ^(Note 5)	E_{AS}	120	mJ	
Avalanche Current ^(Note 1)	I_{AS}	15	A	
Total Dissipation	$T_a=25^\circ\text{C}$	P_{tot}	2	W
	$T_c=25^\circ\text{C}$	P_{tot}	88	W
Junction Temperature	T_j	175	$^\circ\text{C}$	
storage Temperature	T_{stg}	-55~175	$^\circ\text{C}$	
Maximum Temperature for soldering	T_L	300	$^\circ\text{C}$	

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance Junction to Case-sink	R_{thJC}	1.7	$^\circ\text{C/W}$
Thermal Resistance Junction to Ambient	R_{thJA}	62.5	$^\circ\text{C/W}$

4.3 Electrical Characteristics (T_c=25°C, unless otherwise noted)

PARAMETER	SYMBOL	Test Condition	VALUE			UNIT
			MIN	TYP	MAX	
Off Characteristics						
Drain-source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	60	--	--	V
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V, T _C =25°C	--	--	1	μA
		V _{DS} =48V, V _{GS} =0V, T _C =125°C	--	--	100	μA
Gate-to-Source Forward Leakage	I _{GSSF}	V _{GS} =+20V	--	--	100	nA
Gate-to-Source Reverse Leakage	I _{GSSR}	V _{GS} =-20V	--	--	-100	nA
On Characteristics ^(Note 3)						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	--	4	V
Drain-source on Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	--	12	18	mΩ
Dynamic Characteristics ^(Note 4)						
Forward Transfer conductance	g _{fs}	V _{DS} =15V, I _D =10A	--	9.5	--	S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =20V, f=1.0MHz	--	2068	--	pF
Output Capacitance	C _{oss}		--	200	--	
Reverse Transfer Capacitance	C _{rss}		--	150	--	
Gate Resistance	R _G	V _{DS} =0V, V _{GS} =0V, F=1MHz	--	1.4	--	Ω
Switching Characteristics ^(note4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =20Ω, I _D =1A, V _{GS} =10V, R _{GEN} =6Ω	--	14	--	nS
Turn-on Rise Time	t _r		--	13	--	nS
Turn-off Delay Time	t _{d(off)}		--	20	--	nS
Turn-off Fall Time	t _f		--	7.2	--	nS
Total Gate Charge	Q _g	I _D =20A, V _{DS} =20V, V _{GS} =10V	--	51	--	nC
Gate-to-Source Charge	Q _{gs}		--	11	--	
Gate-to-Drain("Miller") Charge	Q _{gd}		--	17	--	
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{FSD}	V _{GS} =0V, I _S =2A	--	--	1.5	V
Diode Forward Current ^(Note 2)	I _S		--	--	2	A
Reverse Recovery Time	t _{rr}	T _J =25°C, I _F =20A, di _F /dt=100A/μs, V _{GS} =0V	--	28	--	nS
Reverse Recovery Charge	Q _{rr}		--	24	--	nC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, t_s≤10sec.
- 3: Pulse width ≤ 300μs, duty cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production.
- 5: L=10mH, I_D=3.58A, V_{DD}=50V, V_{GATE}=600V, Start T_J=25°C.
- 6: I_{SD}=2A, di/dt≤100A/μs, V_{DD}≤BV_{DSS}, Start T_J=25°C.

5 Typical characteristics diagrams

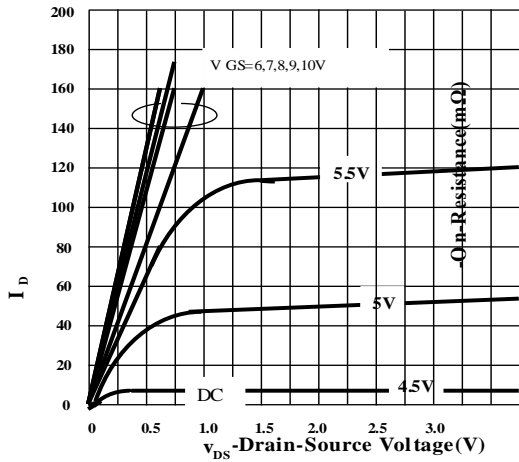


Figure.1 Output Characteristics

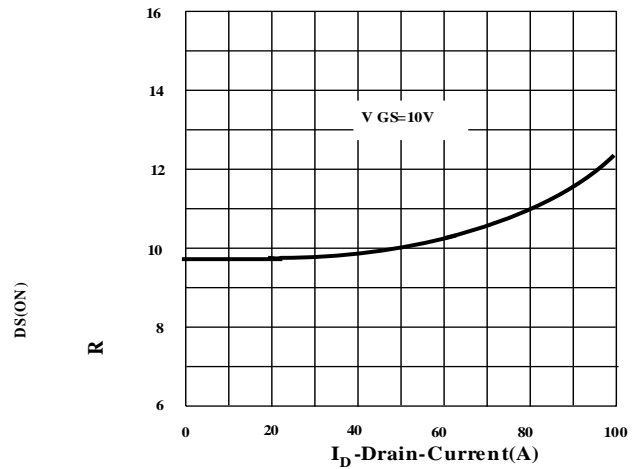


Figure.2 Drain- Source On Resistance

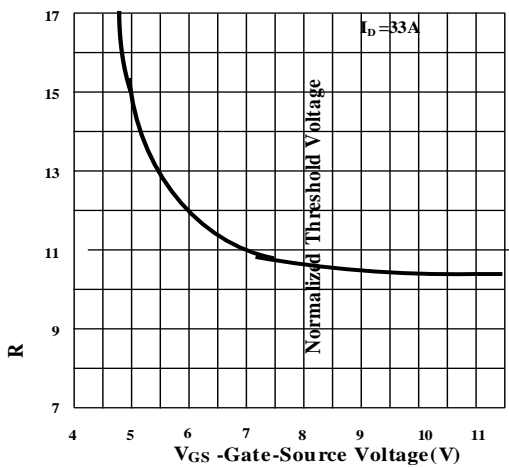


Figure.3 Drain-Source On Resistance

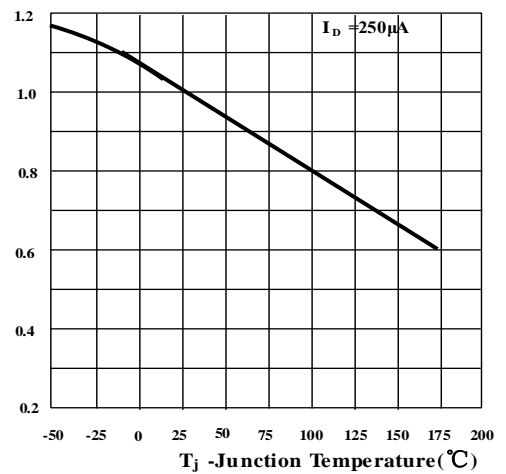


Figure.4 Gate Threshold Voltage

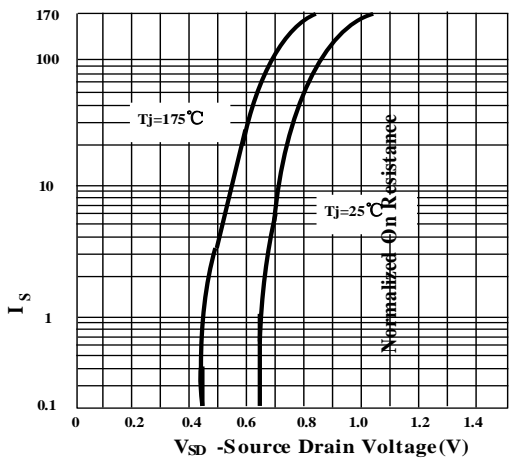


Figure.5 Source- Drain Diode Forward

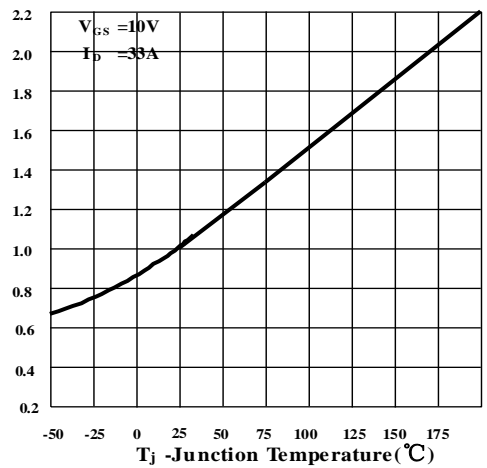


Figure.6 Drain-Source On Resistance

5 Typical characteristics diagrams(continues)

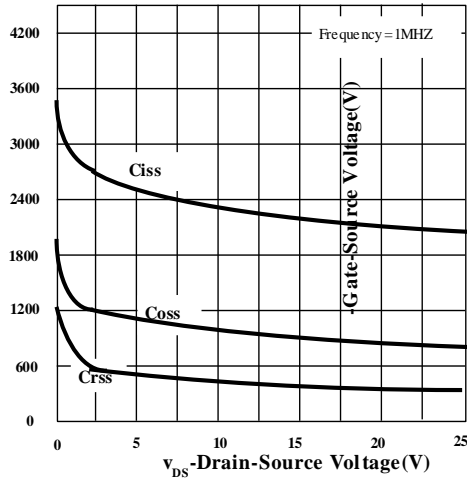


Figure.7 Capacitance

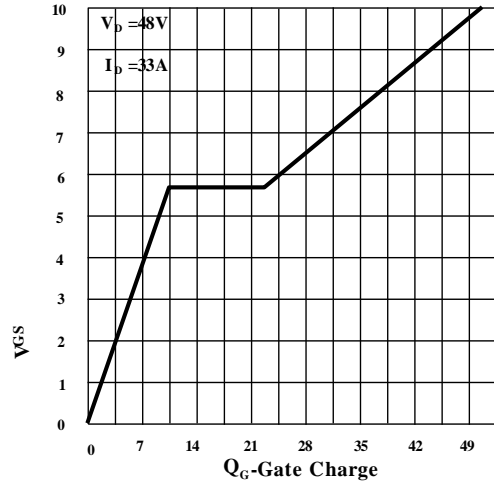


Figure.8 Gate Charge

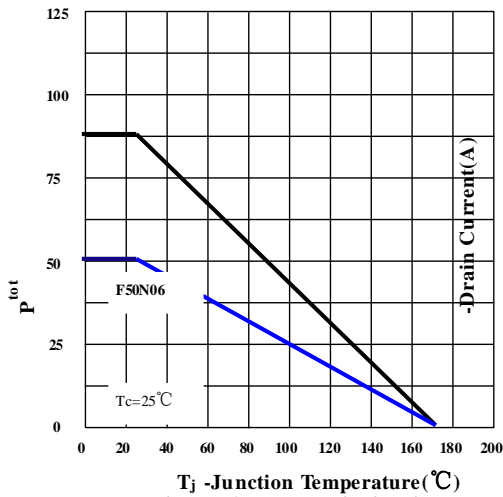


Figure.9 Power Dissipation

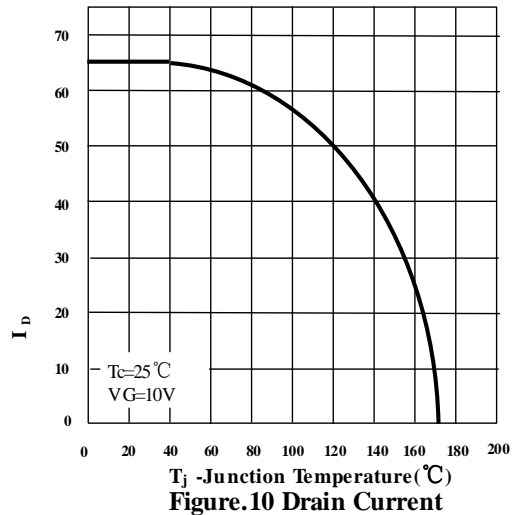


Figure.10 Drain Current

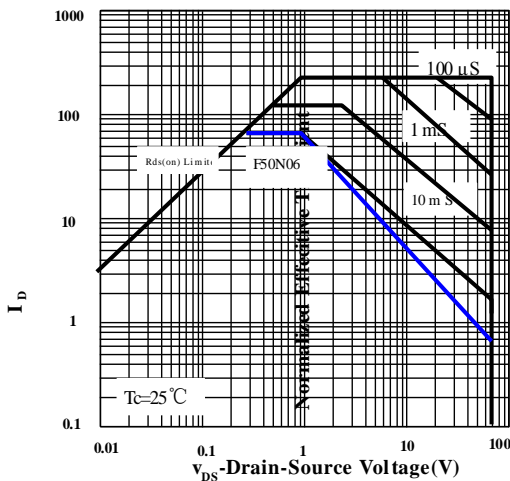


Figure.11 Safe Operation Area

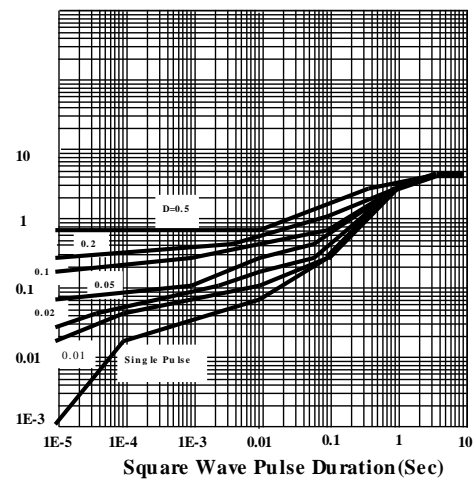
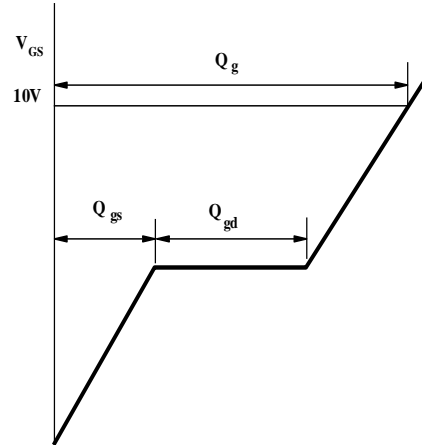
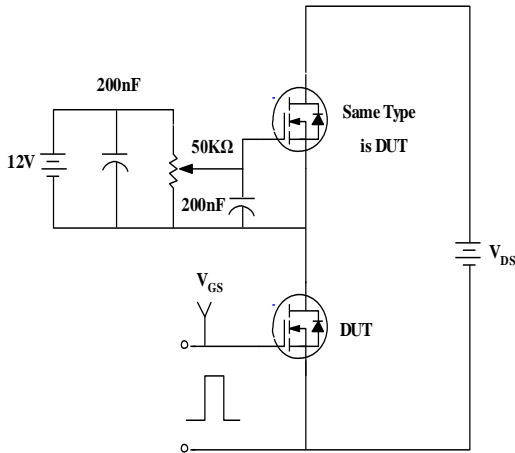
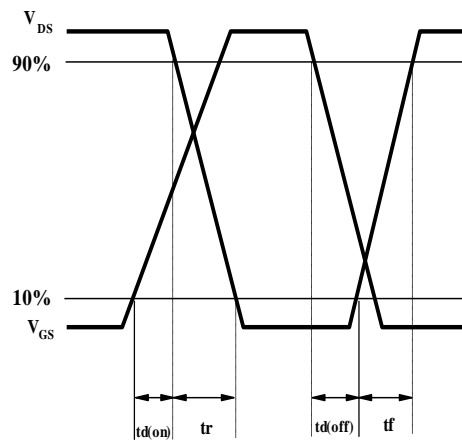
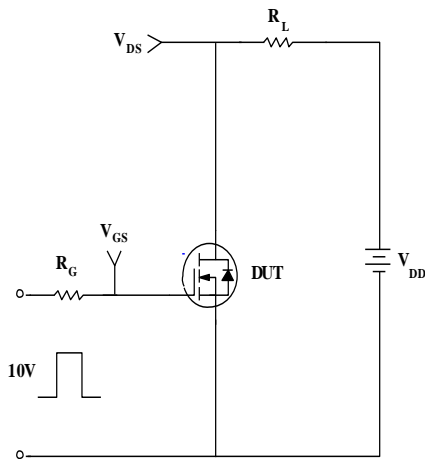


Figure.12 Thermal Transient Impedance

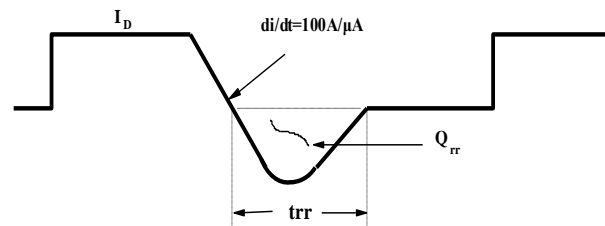
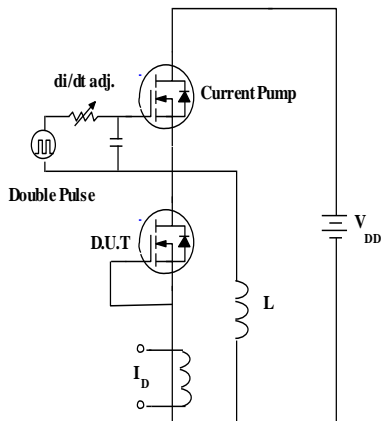
6 Typical Test Circuit and Waveform



1) Gate Charge Test Circuit & Waveform

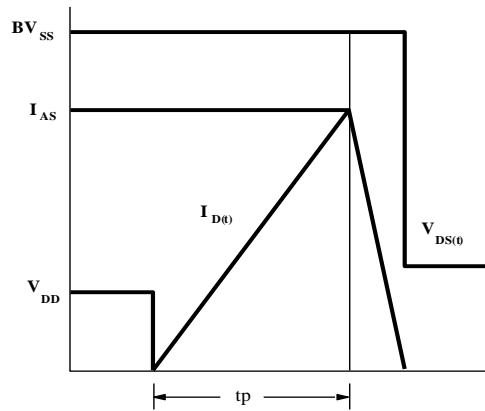
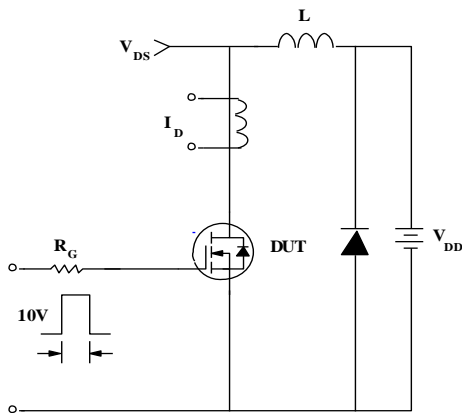


2) Resistive Switching Test Circuit & Waveforms



3) Diode Reverse Recovery Test Circuit & Waveform

6 Typical Test Circuit and Waveform(continues)



4) Unclamped Inductive Switching Test Circuit & Waveforms

7 Product Names Rules

F X X N E X X

Packaging Code
220F: F 220: Nothing
251: B 252: D
262: I 263: E

Rated Voltage Code
With 2 Digital, For Example:
60 on behalf of 600V,
06 on behalf of 60v

Rated Current Code
With 1-2 Digital,
For Example:
4 on behalf of 4A,
10 on behalf of 10A,
08 on behalf of 0.8A

Special Function Code
E on behalf of build-in ESD
Nothing on behalf of not ESD

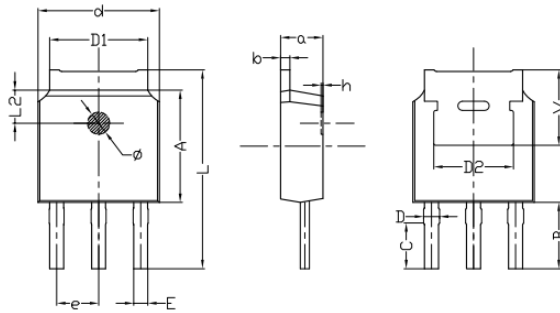
Channel Polarity Code
N on behalf of N channel
P on behalf of P channel

8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
50N06	TO-220C	50N06	Pb-free	Tube	1000/box
F50N06	TO-220F	F50N06	Pb-free	Tube	1000/box
B50N06	TO-251	B50N06	Pb-free	Tube	1000/box
D50N06	TO-252	D50N06	Pb-free	Tape & Reel	3000/box
I50N06	TO-262	I50N06	Pb-free	Tube	1000/box
E50N06	TO-263	E50N06	Pb-free	Tape & Reel	800/box

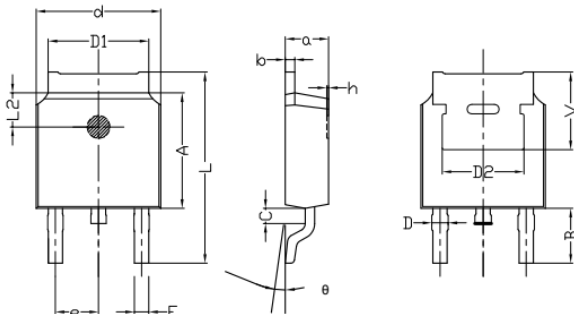
9 Dimensions

TO-251B PACKAGE OUTLINE DIMENSIONS

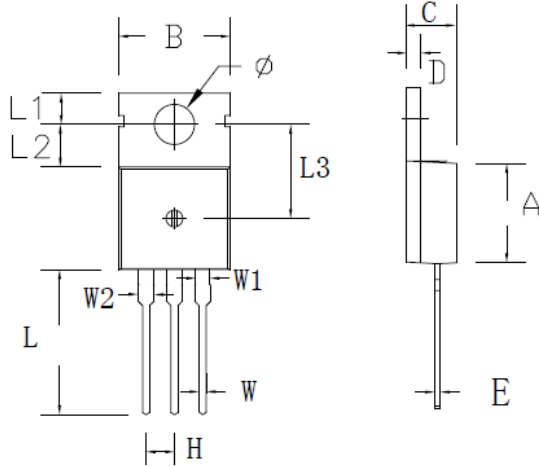


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
a	2.20	2.40	0.087	0.0946
b	0.46	0.58	0.018	0.023
C	2.45	2.65	0.097	0.104
D	0.80	0.90	0.032	0.035
d	6.30	6.70	0.248	0.264
D1	5.00	5.50	0.197	0.217
D2	TYP 4.83		TYP 0.190	
A	5.80	6.20	0.228	0.244
e	2.19	2.39	0.086	0.094
L	10.40	11.00	0.4098	0.4334
B	3.50	3.70	0.1379	0.1458
L2	1.5	1.8	0.059	0.071
φ	1.10	1.30	0.0433	0.0512
h	0.00	0.30	0.000	0.012
V	5.25	5.85	0.207	0.230
E	0.60	0.80	0.0236	0.0315

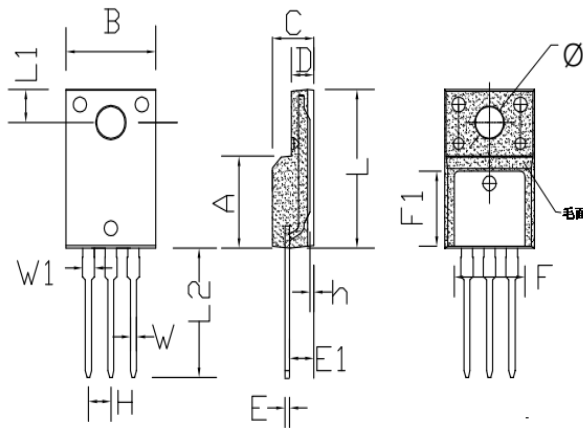
TO-252B PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
a	2.20	2.40	0.087	0.095
b	0.46	0.58	0.018	0.023
c	0.70	0.90	0.028	0.035
D	0.80	1.00	0.032	0.039
d	6.30	6.70	0.248	0.264
D1	5.00	5.50	0.197	0.217
D2	TYP 4.83		TYP 0.190	
A	5.80	6.20	0.228	0.244
e	2.19	2.39	0.086	0.094
L	9.40	10.40	0.370	0.409
B	2.6	3.2	0.102	0.126
L2	1.5	1.8	0.059	0.071
θ	0	8	0	8
h	0	0.3	0	0.012
V	5.25	5.85	0.207	0.230

9 Dimensions(continues)
TO-220C PACKAGE OUTLINE DIMENSIONS


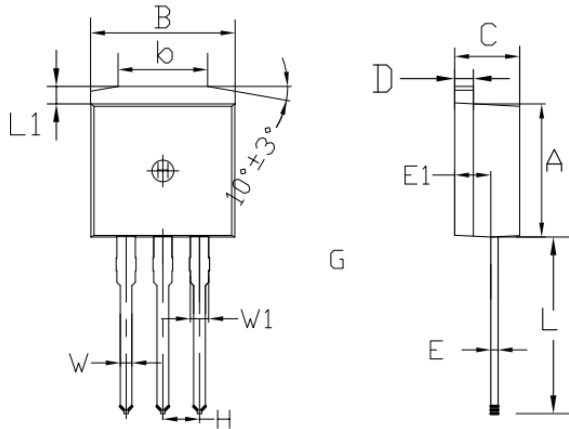
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
H	2.54 TYP		0.100 TYP	
W	0.60	0.95	0.024	0.037
W1	1.05	1.45	0.041	0.057
W2	1.20	1.60	0.047	0.063
L	12.60	13.40	0.496	0.528
L1	2.45	2.95	0.096	0.116
L2	3.45	3.95	0.136	0.156
L3	8.15	8.65	0.321	0.341
phi	3.50	3.90	0.138	0.154

TO-220F PACKAGE OUTLINE DIMENSIONS


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	10.00	10.50	0.394	0.413
C	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
H	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
phi	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

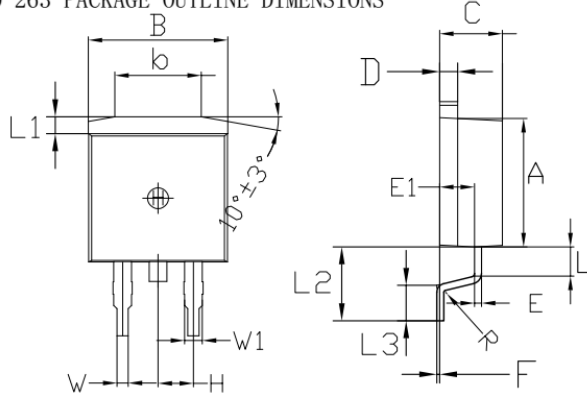
9 Dimensions(continues)

TO-262 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	12.25	13.75	0.482	0.541
L1	1.15	1.45	0.045	0.057
E1	2.4	2.6	0.0945	0.1024
W	0.80	0.82	0.0315	0.034
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256

TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	1.90	2.30	0.075	0.091
L1	1.15	1.45	0.045	0.057
R	0.24	0.26	0.0095	0.0102
W	0.80	0.82	0.0315	0.0323
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256
E1	2.4	2.6	0.0946	0.1024
L2	5.20	5.80	0.205	0.228
L3	2.20	3.20	0.087	0.126
F	0.03	0.23	0.0012	0.0091

10 Attentions

- ROUM Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Roma products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2017.03.14	1.0	Original	